


Sheet 1 of <b>FIRST IDS LIST OF REFERENCES          CITED BY APPLICANT          (FORM PTO-1449)</b> <b>DATED: May 18, 2005</b>				Atty. Docket No. 4878/PCT		<b>107535741</b> <small>Serial No. to be assigned</small>		
Applicant: Seiji NAKAHATA et al.						U.S. Filing Date: May 18, 2005		Art Unit: 2812
U. S. PATENT DOCUMENTS								
*EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	Cl.	Sub- Cl.	Fil. Date	
FOREIGN PATENT DOCUMENTS								
		DOCUMENT NO.	DATE	COUNTRY	Cl.	Sub- Cl.	Trans.	
							Yes	No
GA	AA	01-204425	08/1989	Japan	-	-	Abst	
GA	AB	WO 02/101121	12/2002	PCT	-	-	Engl.	
OTHER DOCUMENTS								
GA	AC	Mikio Yamamoto, Handbook of Crystal Engineering First Edition, Kyoritsu Shuppan Co., Ltd., 1990 pp. 421-423 with English Translation of Table VI-6-1						
GA	AD	J.L. Weyher, et al., Chemical polishing of bulk and epitaxial GaN, Journal of Crystal Growth, 182 (1997), pages 17 to 22						
EXAMINER'S SIGNATURE					DATE CONSIDERED			
					6/24/07			
<small>*EXAMINER: Initial if reference considered; whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>								

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